

IN THE CLAIMS

Please amend the claims as follows:

1. (currently amended) A method for producing a preform from synthetic quartz glass by means of a plasma-assisted deposition process, said method comprising: supplying [~~in that~~] a hydrogen-free media flow containing a glass starting material and a carrier gas [~~is supplied~~] to a multi-nozzle deposition burner, introducing the glass starting material [~~is introduced~~] by means of the deposition burner into a plasma zone [~~and is~~] wherein the glass starting material is oxidized so as to form [~~therein while forming~~] SiO₂ particles, and depositing the SiO₂ particles [~~are deposited~~] on a deposition surface while being directly vitrified, wherein [~~characterized in that~~] the media flow is focused by means of the deposition burner [(1)] towards the plasma zone [(4)].
2. (currently amended) The method according to claim 1, wherein [~~characterized in that~~] the media flow is focused onto the plasma zone [(4)] by means of a media nozzle [(7)] of the deposition burner [(1)] that tapers in the direction of [~~is tapering towards~~] the plasma zone [(4)].
3. (currently amended) The method according to claim 2, wherein [~~characterized in that~~] when exiting from the media nozzle [(7)] the media flow is enveloped by an oxygen-containing working gas flow.
4. (currently amended) The method according to claim 3, wherein [~~characterized in that~~] the working gas flow turbulently exits from a first working gas nozzle [(14)] of the deposition burner [(1)] that is designed as a diffuser.

5. (currently amended) The method according to claim 3, wherein ~~[characterized in that]~~ when exiting from the working gas nozzle [(14)] the working gas flow is enveloped by at least one oxygen-containing separating gas flow exiting from an annular gap nozzle [(17)] coaxially surrounding the working gas nozzle [(14)].
6. (currently amended) The method according to claim 3, wherein ~~[characterized in that]~~ the plasma zone [(4)] is produced by means of high-frequency excitation [(3)] inside a burner tube [(2)] into which a mixture of media flow and working gas flow is introduced.
7. (currently amended) The method according to claim 1, wherein ~~[characterized in that]~~ the glass starting material in the media flow contains silicon tetrachloride (SiCl_4) and the carrier gas is nitrogen ~~[as the carrier gas]~~.
8. (currently amended) The method according to claim 1, wherein ~~[characterized in that]~~ the glass starting material contains a fluorine-containing component.
9. (currently amended) A device for producing a preform from synthetic quartz glass by means of a plasma-assisted deposition process ~~[performing the method according to claim 1]~~, said device comprising an excitation source ~~[for]~~ producing a plasma zone, and a multi-nozzle deposition burner which has a central axis and which is provided with a media nozzle ~~[for the supply of]~~ supplying a a hydrogen-free media flow containing a glass starting material and a carrier gas to the plasma zone, wherein ~~[characterized in that]~~ the media nozzle [(7)] is configured to focus towards the plasma zone [(4)].
10. (currently amended) The device according to claim 9, wherein ~~[characterized in that]~~ the media nozzle [(7)] tapers in a tapering portion ~~[area (6)]~~ towards the plasma zone [(4)].

11. (currently amended) The device according to claim 10, wherein [~~characterized in that~~] the tapering portion [~~area (6)~~] has a length of at least 5 mm [~~, preferably at least 8 mm~~].
12. (currently amended) The device according to claim 9, wherein [~~characterized in that~~] the media nozzle [(7)] has a nozzle opening with a diameter ranging between 4.5 mm and 6.5 mm [~~, preferably between 5.0 mm and 6.0 mm~~].
13. (currently amended) The device according to claim 9, wherein [~~characterized in that~~] the media nozzle [(7)] is configured [~~designed~~] as a central middle nozzle and is coaxially surrounded by a working gas nozzle [(14) ~~in the form of~~] defining therebetween an annular gap and which is configured [~~designed~~] as a diffuser and continuously expands in an expansion portion [~~area~~] towards the plasma zone [(4)].
14. (currently amended) The device according to claim 13, wherein [~~characterized in that~~] the expansion portion [~~area~~] has a length of at least 5 mm [~~, preferably at least 8 mm~~].
15. (currently amended) The device according to claim 12, wherein [~~characterized in that~~] the media nozzle [(7)] has a nozzle opening which extends in a first nozzle plane extending in a direction perpendicular to the central axis [(9)], and that the working gas nozzle [(14)] has a nozzle opening which extends in a second nozzle plane extending in a direction perpendicular to the central axis, the first nozzle plane, when viewed in the direction of flow, being arranged upstream of the second nozzle plane by a length between 5 mm and 35 mm [~~, preferably between 13 mm and 33 mm~~].
16. (currently amended) The device according to claim 9, wherein [~~characterized in that~~] the media nozzle [(7)] is formed by a quartz glass tube.

17. (currently amended) The device according to claim 9, wherein ~~[characterized in that]~~ the media nozzle ~~[(7)]~~ is designed as a central middle nozzle and is coaxially surrounded by at least two annular gap nozzles ~~[(14; 17) for the supply of]~~ supplying oxygen to the plasma zone ~~[(4)]~~
18. (new) The device according to claim 10, wherein the tapering area has a length of at least 8 mm.
19. (new) The device according to claim 9, wherein the media nozzle has a nozzle opening with a diameter ranging between 5.0 mm and 6.0 mm.
20. (new) The device according to claim 13, wherein the expansion portion has a length of at least 8 mm.
21. (new) The device according to claim 12, wherein the media nozzle has a nozzle opening which extends in a first nozzle plane extending in a direction perpendicular to the central axis, and that the working gas nozzle has a nozzle opening which extends in a second nozzle plane extending in a direction perpendicular to the central axis, the first nozzle plane, when viewed in the direction of flow, being arranged upstream of the second nozzle plane by a length between 13 mm and 33 mm.